

# DS160PR410-Q1 PCIe® 4.0 Automotive 4-Channel Linear Redriver

## 1 Features

- Four-channel linear redriver supporting PCIe® 4.0
  - Backward compatible to PCIe 3.0, 2.0, 1.0
- Protocol agnostic linear equalizer supporting most AC coupled interfaces up to 20Gbps
- Integrated two 2x2 Crosspoint mux function
- 12dB PCIe 4.0 reach extension over PVT with 16dB CTLE boost
- Ultra-low latency of 100ps
- Excellent performance at 16Gbps (8GHz Nyquist)
  - -15 / -20dB Rx / Tx return loss
  - 1200mV AC linearity
- High BW resulting excellent linear EQ curves
- Single 3.3V supply with 160mW/chan active power
- Immunity to supply noise with internal voltage regulator
- Automatic receiver detection for PCIe use cases
- Linear redriver allows seamless support for PCIe link training
- Support for x4, x8, x16 bus width in pin mode, and x1, x2, x4, x8, x16 in I<sup>2</sup>C mode
- Pin-strap, SMBus or EEPROM programming
  - 18 EQ boost 5 flat gain settings
- -40 to 105°C (grade 2) ambient temperature support without heatsink
- 5mm x 7mm automotive friendly package with 0.5 mm pitch and wettable flank

## 2 Applications

- Automotive [Advanced driver assistance systems \(ADAS\)](#)
- Automotive [Infotainment & cluster](#)

## 3 Description

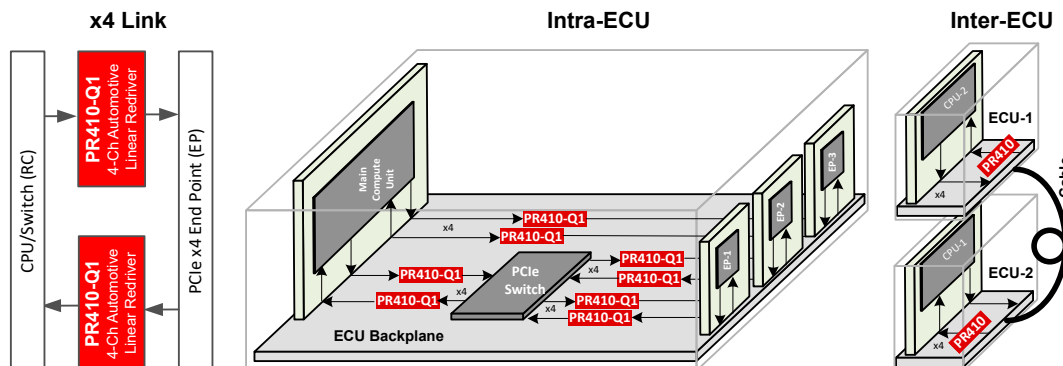
The DS160PR410-Q1 is a four channel low-power high-performance linear redriver with integrated two 2x2 cross-point mux designed to support PCIe® 4.0 and other interfaces up to 20Gbps.

The DS160PR410-Q1 receivers deploy continuous time linear equalizers (CTLE) to provide a programmable high-frequency boost. The equalizer can open an input eye that is completely closed due to inter-symbol interference (ISI) induced by an interconnect medium, such as PCB traces. The CTLE receiver is followed by a linear output driver. The linear data-paths of DS160PR410-Q1 preserve transmit preset signal characteristics. The linear redriver becomes part of the passive channel that as a whole get link trained for best transmit and receive equalization settings. This transparency in the link training protocol results in best electrical link and lowest possible latency. Low channel-channel cross-talk, low additive jitter and excellent return loss makes the device almost a passive element in the link, but with its useful equalization. The data-path of the device uses an internally regulated power rail that provides high immunity to any supply noise on the board. The device also has low AC and DC gain variation providing consistent equalization in high volume platform deployment.

### Package Information

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>
DS160PR410-Q1	VQFN (RGF, 40)	5mm × 7mm

- (1) For all available packages, see the orderable addendum at the end of the data sheet.
- (2) The package size (length × width) is a nominal value and includes pins, where applicable.

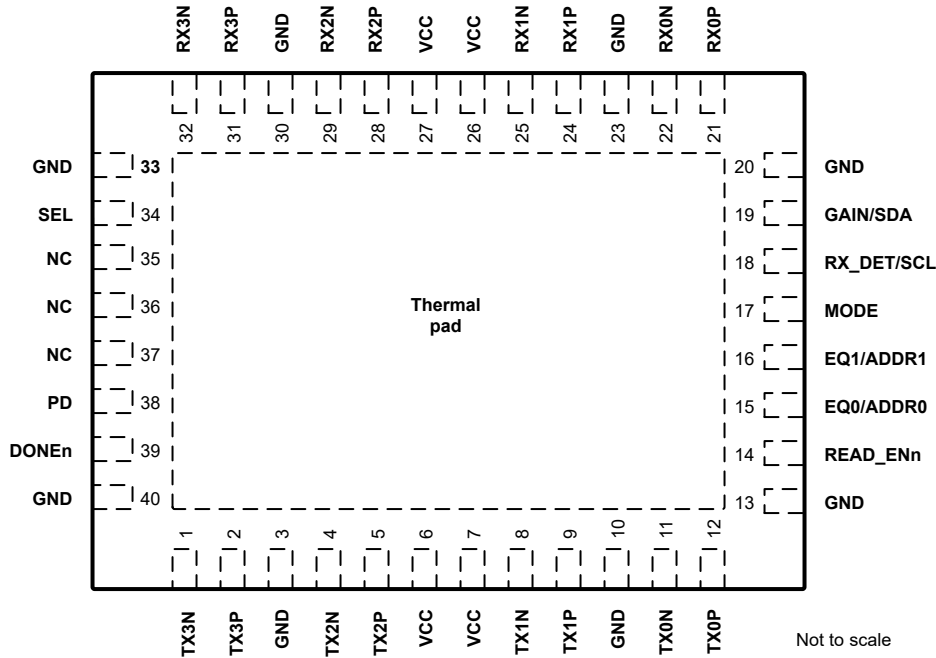


**Typical Applications**

## Table of Contents

<b>1 Features</b> .....	1	6.4 Device Functional Modes.....	15
<b>2 Applications</b> .....	1	6.5 Programming.....	16
<b>3 Description</b> .....	1	<b>7 Application and Implementation</b> .....	21
<b>4 Pin Configuration and Functions</b> .....	3	7.1 Application Information.....	21
<b>5 Specifications</b> .....	6	7.2 Typical Applications.....	21
5.1 Absolute Maximum Ratings.....	6	7.3 Power Supply Recommendations.....	26
5.2 ESD Ratings.....	6	7.4 Layout.....	26
5.3 Recommended Operating Conditions.....	6	<b>8 Device and Documentation Support</b> .....	28
5.4 Thermal Information.....	7	8.1 Documentation Support.....	28
5.5 DC Electrical Characteristics.....	7	8.2 Receiving Notification of Documentation Updates....	28
5.6 High Speed Electrical Characteristics.....	8	8.3 Support Resources.....	28
5.7 SMBUS/I <sup>2</sup> C Timing Characteristics.....	9	8.4 Trademarks.....	28
5.8 Typical Characteristics.....	11	8.5 Electrostatic Discharge Caution.....	28
5.9 Typical Jitter Characteristics.....	11	8.6 Glossary.....	28
<b>6 Detailed Description</b> .....	12	<b>9 Revision History</b> .....	28
6.1 Overview.....	12	<b>10 Mechanical, Packaging, and Orderable Information</b> .....	28
6.2 Functional Block Diagram.....	12		
6.3 Feature Description.....	13		

## 4 Pin Configuration and Functions



**Figure 4-1. RGF Package, 40-Pin VQFN (Top View)**

**Table 4-1. Pin Functions**

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
<b>Control Interface</b>			
READ_ENn	14	I, 3.3V LVC MOS	<p><b>In SMBus/I<sup>2</sup>C Controller mode:</b> After device power up, when the pin is low, this initiates the SMBus / I<sup>2</sup>C Controller mode EEPROM read function. When EEPROM read is complete (indicated by assertion of DONEn low), this pin can be held low for normal device operation. During the EEPROM load process the device's signal path is disabled.</p> <p><b>In SMBus/I<sup>2</sup>C Target and Pin modes:</b> In these modes the pin is not used. The pin can be left floating. The pin has internal 1MΩ weak pull-down resistor.</p>
EQ0 / ADDR0	15	I, 5-level	<p><b>In Pin mode:</b> Sets receiver linear equalization (CTLE) boost provided in <a href="#">Table 6-1</a>. These pins are sampled at device power-up only.</p>
EQ1 / ADDR1	16	I, 5-level	<p><b>In SMBus/I<sup>2</sup>C mode:</b> Sets SMBus / I<sup>2</sup>C target address as provided in <a href="#">Table 6-5</a>. These pins are sampled at device power-up only.</p>
MODE	17	I, 5-level	<p>Sets device control configuration modes. 5-level IO pin as provided in <a href="#">Table 6-4</a>. The pin can be exercised at device power up or in normal operation mode.</p> <p>L0: <b>Pin mode</b> – device control configuration is done solely by strap pins.</p> <p>L1: <b>SMBus/I<sup>2</sup>C Controller mode</b> – device control configuration is read from external EEPROM. When the DS160PR410-Q1 has finished reading from the EEPROM successfully, the chip drives the DONEn pin LOW. SMBus/I<sup>2</sup>C target function is available in this mode before, during or after EEPROM reading. Note: during EEPROM reading if the external SMBus/I<sup>2</sup>C controller wants to access DS160PR410-Q1 registers it must support arbitration.</p> <p>L2: <b>SMBus/I<sup>2</sup>C Target mode</b> – device control configuration is done by an external SMBus/I<sup>2</sup>C controller.</p> <p>L3 and L4 (Float): RESERVED – TI internal test modes.</p>

**Table 4-1. Pin Functions (continued)**

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
RX_DET / SCL	18	I, 5-level / I/O, 3.3V LVCMOS, open drain	<b>In Pin mode:</b> Sets receiver detect state machine options as provided in Table 6-3. The pin is sampled at device power-up only. <b>In SMBus/I<sup>2</sup>C mode:</b> 3.3V SMBus/I <sup>2</sup> C clock. External 1kΩ to 5kΩ pullup resistor is required as per SMBus / I <sup>2</sup> C interface standard.
GAIN / SDA	19	I, 5-level / I/O, 3.3V LVCMOS, open drain	<b>In Pin mode:</b> Flat gain (DC and AC) from the input to the output of the device. The pin is sampled at device power-up only. <b>In SMBus/I<sup>2</sup>C mode:</b> 3.3V SMBus/I <sup>2</sup> C data. External 1kΩ to 5kΩ pullup resistor is required as per SMBus / I <sup>2</sup> C interface standard.
SEL	34	I, 3.3V LVCMOS	The pin selects the cross-point mux paths. Active in all device control modes. 59kΩ internal pull-down. Note: the pin also triggers PCIe RX detect state machine when toggled. For PCIe redriver use cases without mux function leave the pin unconnected. Low: straight data path – RX[0/1/2/3][P/N] connected to TX[0/1/2/3][P/N] through the redriver. High: cross data path – RX[0/1/2/3][P/N] connected to TX[1/0/3/2][P/N] through the redriver.
PD	38	I, 3.3V LVCMOS	2-level logic controlling the operating state of the redriver. Active in all device control modes. The pin has internal 1MΩ weak pull-down resistor. The pin triggers PCIe Rx detect state machine when toggled. High: power down Low: power up, normal operation
DONE <sub>En</sub>	39	O, 3.3V open drain	<b>In SMBus/I<sup>2</sup>C Controller mode:</b> Indicates the completion of a valid EEPROM register load operation. External pullup resistor such as 4.7kΩ required for operation. High: External EEPROM load failed or incomplete Low: External EEPROM load successful and complete <b>In SMBus/I<sup>2</sup>C Target/Pin mode:</b> This output is High-Z. The pin can be left floating.
<b>Data Interface</b>			
TX3N	1	O	Inverting pin for 100Ω differential driver output. Channel 3.
TX3P	2	O	Non-inverting pin for 100Ω differential driver output. Channel 3.
TX2N	4	O	Inverting pin for 100Ω differential driver output. Channel 2.
TX2P	5	O	Non-inverting pin for 100Ω differential driver output. Channel 2.
TX1N	8	O	Inverting pin for 100Ω differential driver output. Channel 1.
TX1P	9	O	Non-inverting pin for 100Ω differential driver output. Channel 1.
TX0N	11	O	Inverting pin for 100Ω differential driver output. Channel 0.
TX0P	12	O	Non-inverting pin for 100Ω differential driver output Channel 0.
RX0P	21	I	Non-inverting differential inputs to the equalizer. Integrated 50Ω termination resistor from the pin to internal CM bias voltage. Channel 0.
RX0N	22	I	Inverting differential inputs to the equalizer. Integrated 50Ω termination resistor from the pin to internal CM bias voltage. Channel 0.
RX1P	24	I	Non-inverting differential inputs to the equalizer. Integrated 50Ω termination resistor from the pin to internal CM bias voltage. Channel 1.
RX1N	25	I	Inverting differential inputs to the equalizer. Integrated 50Ω termination resistor from the pin to internal CM bias voltage. Channel 1.
RX2P	28	I	Non-inverting differential inputs to the equalizer. Integrated 50Ω termination resistor from the pin to internal CM bias voltage. Channel 2.
RX2N	29	I	Inverting differential inputs to the equalizer. Integrated 50Ω termination resistor from the pin to internal CM bias voltage. Channel 2.
RX3P	31	I	Non-inverting differential inputs to the equalizer. Integrated 50Ω termination resistor from the pin to internal CM bias voltage. Channel 3.

**Table 4-1. Pin Functions (continued)**

PIN		TYPE <sup>(1)</sup>	DESCRIPTION
NAME	NO.		
RX3N	32	I	Inverting differential inputs to the equalizer. Integrated 50Ω termination resistor from the pin to internal CM bias voltage. Channel 3.
<b>Power, other</b>			
GND	EP, 3, 10, 13, 20, 23, 30, 33, 40	G	Ground reference for the device. EP: the Exposed Pad at the bottom of the QFN package. This is used as the GND return for the device. The EP must be connected to one or more ground planes through the low resistance path. A via array provides a low impedance path to GND. The EP also improves thermal dissipation.
VCC	6, 7, 26, 27	P	Power supply pins. VCC = 3.3V ±10%. The VCC pins on this device must be connected through a low-resistance path to the board VCC plane. Install a decoupling capacitor to GND near each VCC pin.
NC	35, 36, 37	-	No connect. Leave floating.

(1) I = input, O = output, P = power, G = ground

## 5 Specifications

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
VCC_ABSMAX	Supply voltage (VCC)	-0.5	4.0	V
VIO_CMOS_ABSMAX	3.3V LVCMOS and open drain I/O voltage	-0.5	4.0	V
VIO_5LVL_ABSMAX	5-level input I/O voltage	-0.5	2.75	V
VIO_HS-RX_ABSMAX	High-speed I/O voltage (RXnP, RXnN)	-0.5	3.2	V
VIO_HS-TX_ABSMAX	High-speed I/O voltage (TXnP, TXnN)	-0.5	2.75	V
T_J_ABSMAX	Junction temperature		150	°C
T_stg	Storage temperature range	-65	150	°C

- (1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

### 5.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000	V
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	±500	

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process. Pins listed as ±2kV may actually have higher performance.  
 (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

### 5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
VCC	Supply voltage, VCC to GND	DC plus AC power must not exceed these limits	3.0	3.3	3.6	V
N <sub>VCC</sub> <sup>(1)</sup>	Supply noise tolerance	DC to <50Hz, sinusoidal			250	mVpp
		50Hz to 500kHz, sinusoidal			100	mVpp
		500kHz to 2.5MHz, sinusoidal			33	mVpp
		Supply noise, >2.5MHz, sinusoidal			10	mVpp
T <sub>RampVCC</sub>	VCC supply ramp time	From 0V to 3.0V	0.150		100	ms
T <sub>A</sub>	Operating ambient temperature		-40		105	°C
T <sub>J</sub>	Operating junction temperature				125	°C
PW <sub>LVCMOS</sub>	Minimum pulse width required for the device to detect a valid signal on LVCMOS inputs	PD, SEL, and READ_ENn	200			µs
VCC <sub>SMBUS</sub>	SMBus/I <sup>2</sup> C SDA and SCL open-drain termination voltage	Supply voltage for open-drain pullup resistor			3.6	V
F <sub>SMBus</sub>	SMBus/I <sup>2</sup> C clock (SCL) frequency	SMBus Target mode	10		400	kHz
VID <sub>LAUNCH</sub>	Source launch amplitude	Differential signaling			1200	mVpp

### 5.3 Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
DR	Data rate	1		20	Gbps

- (1) Sinusoidal noise is superimposed to supply voltage with negligible impact to device function or critical performance shown in the Electrical Table. Steps must be taken to ensure the combined AC plus DC supply noise meets the specified VDD supply voltage limits.

### 5.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		DS160PR4 10-Q1	UNIT
		RGF, 40 Pins	
R <sub>θJA</sub> -High K	Junction-to-ambient thermal resistance	29.6	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	19.0	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	11.2	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	0.4	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	11.1	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	3.8	°C/W

- (1) For more information about traditional and new thermal metrics, see the [IC Package Thermal Metrics application report](#).

### 5.5 DC Electrical Characteristics

over operating free-air temperature and voltage range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>Power</b>						
P <sub>ACT</sub>	Device active power	4 channels active, EQ = 0-2		0.57	0.71	W
		4 channels active, EQ = 5-19		0.69	0.85	W
P <sub>STBY</sub>	Device power consumption in standby power mode	All channels disabled (PD = H)		17	25	mW
<b>Control IO</b>						
V <sub>IH</sub>	High level input voltage	SDA, SCL, PD, READ_ENn, SEL pins	2.1			V
V <sub>IL</sub>	Low level input voltage	SDA, SCL, PD, READ_ENn, SEL pins			1.08	V
V <sub>OH</sub>	High level output voltage	R <sub>pullup</sub> = 4.7kΩ (SDA, SCL, DONEn pins)	2.1			V
V <sub>OL</sub>	Low level output voltage	I <sub>OL</sub> = -4mA (SDA, SCL, DONEn pins)			0.4	V
I <sub>IH,SEL</sub>	Input high leakage current for SEL pins	V <sub>Input</sub> = SEL pins			100	μA
I <sub>IH</sub>	Input high leakage current	V <sub>Input</sub> = VCC, (SCL, SDA, PD, READ_ENn pins)			10	μA
I <sub>IL</sub>	Input low leakage current	V <sub>Input</sub> = 0V, (SCL, SDA, PD, READ_ENn, SEL pins)	-10			μA
I <sub>IH,FS</sub>	Input high leakage current for fail safe input pins	V <sub>Input</sub> = 3.6V, VCC = 0V, (SCL, SDA, PD, READ_ENn, SEL pins)			200	μA
C <sub>IN-CTRL</sub>	Input capacitance	SDA, SCL, PD, READ_ENn, SEL pins		1.6		pF
<b>5 Level IOs (MODE, GAIN, EQ0, EQ1 pins)</b>						
I <sub>IH_5L</sub>	Input high leakage current, 5-level IOs	VIN = 2.5V			10	μA
I <sub>IL_5L</sub>	Input low leakage current for all 5-level IOs except MODE.	VIN = GND	-10			μA
I <sub>IL_5L,MODE</sub>	Input low leakage current for MODE pin	VIN = GND	-200			μA

## 5.5 DC Electrical Characteristics (continued)

over operating free-air temperature and voltage range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>Receiver</b>						
$V_{RX-DC-CM}$	RX DC common mode voltage	Device is in active or standby state		1.4		V
$Z_{RX-DC}$	Rx DC single-ended impedance			50		$\Omega$
<b>Transmitter</b>						
$Z_{TX-DIFF-DC}$	DC differential Tx impedance	Impedance of Tx during active signaling, VID,diff = 1Vpp		100		$\Omega$
$V_{TX-DC-CM}$	Tx DC common mode voltage			1.0		V
$I_{TX-SHORT}$	Tx short circuit current	Total current the Tx can supply when shorted to GND		70		mA

## 5.6 High Speed Electrical Characteristics

over operating free-air temperature and voltage range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>Receiver</b>						
$RL_{RX-DIFF}$	Input differential return loss	50MHz		-27		dB
		4.0GHz		-15		dB
		5.0GHz		-15		dB
		8.0GHz		-15		dB
		10.0GHz		-11		dB
$RL_{RX-CM}$	Input common mode return loss	50MHz		-22		dB
		4.0GHz		-12		dB
		5.0GHz		-11		dB
		8.0GHz		-10		dB
		10.0GHz		-8		dB
$XT_{RX}$	Receiver-side pair-to-pair isolation	Minimum over 10.0MHz to 10.0GHz range		-50		dB
<b>Transmitter</b>						
$RL_{TX-DIFF}$	Output differential return loss	50.0MHz		-29		dB
		4.0GHz		-16		dB
		5.0GHz		-17		dB
		8.0GHz		-20		dB
		10.0GHz		-18		dB
$RL_{TX-CM}$	Output common mode return loss	50.0MHz		-16		dB
		4.0GHz		-11		dB
		5.0GHz		-10		dB
		8.0GHz		-9		dB
		10.0GHz		-9		dB
$XT_{TX}$	Transmit-side pair-to-pair isolation	Minimum over 10.0MHz to 10.0GHz range		-46		dB
<b>Device Datapath</b>						
$T_{PLHD/PHLD}$	Input-to-output latency (propagation delay) through a data channel	For either low-to-high or high-to-low transition		100		ps
$T_{RJ-DATA}$	Additive random jitter with data	Jitter through redriver minus the calibration trace. 20Gbps PRBS15. 800mVpp-diff input swing		70		fs

## 5.6 High Speed Electrical Characteristics (continued)

over operating free-air temperature and voltage range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
XT	Channel to channel xtalk (between adjacent active channels, FEXT)	Minimum over 50.0MHz to 10.0Ghz range, normalized to EQ gain of 0dB		-38		dB
LINEARITY-DC	Output DC linearity			1650		mVpp
LINEARITY-AC	Output AC linearity at GAIN = L4	8Gbps		1250		mVpp
LINEARITY-AC	Output AC linearity at GAIN = L4	16Gbps		1200		mVpp
LINEARITY-AC	Output AC linearity at GAIN = L4	20Gbps		1100		mVpp

## 5.7 SMBUS/I<sup>2</sup>C Timing Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>Target Mode</b>						
t <sub>SP</sub>	Pulse width of spikes which must be suppressed by the input filter				50	ns
t <sub>HD-STA</sub>	Hold time (repeated) START condition. After this period, the first clock pulse is generated		0.6			μs
t <sub>LOW</sub>	LOW period of the SCL clock		1.3			μs
T <sub>HIGH</sub>	HIGH period of the SCL clock		0.6			μs
t <sub>SU-STA</sub>	Setup time for a repeated START condition		0.6			μs
t <sub>HD-DAT</sub>	Data hold time		0			μs
T <sub>SU-DAT</sub>	Data setup time		0.1			μs
t <sub>r</sub>	Rise time of both SDA and SCL signals	Pullup resistor = 4.7kΩ, C <sub>b</sub> = 10pF		120		ns
t <sub>f</sub>	Fall time of both SDA and SCL signals	Pullup resistor = 4.7kΩ, C <sub>b</sub> = 10pF		2		ns
t <sub>SU-STO</sub>	Setup time for STOP condition		0.6			μs
t <sub>BUF</sub>	Bus free time between a STOP and START condition		1.3			μs
t <sub>VD-DAT</sub>	Data valid time				0.9	μs
t <sub>VD-ACK</sub>	Data valid acknowledge time				0.9	μs
C <sub>b</sub>	Capacitive load for each bus line				400	pF
<b>Controller Mode</b>						
f <sub>SCL-M</sub>	SCL clock frequency			303		kHz
t <sub>LOW-M</sub>	SCL low period			1.90		μs
T <sub>HIGH-M</sub>	SCL high period			1.40		μs
t <sub>SU-STA-M</sub>	Setup time for a repeated START condition			2		μs
t <sub>HD-STA-M</sub>	Hold time (repeated) START condition. After this period, the first clock pulse is generated			1.5		μs
T <sub>SU-DAT-M</sub>	Data setup time			1.4		μs
t <sub>HD-DAT-M</sub>	Data hold time			0.5		μs
t <sub>R-M</sub>	Rise time of both SDA and SCL signals	Pullup resistor = 4.7kΩ, C <sub>b</sub> = 10pF		120		ns

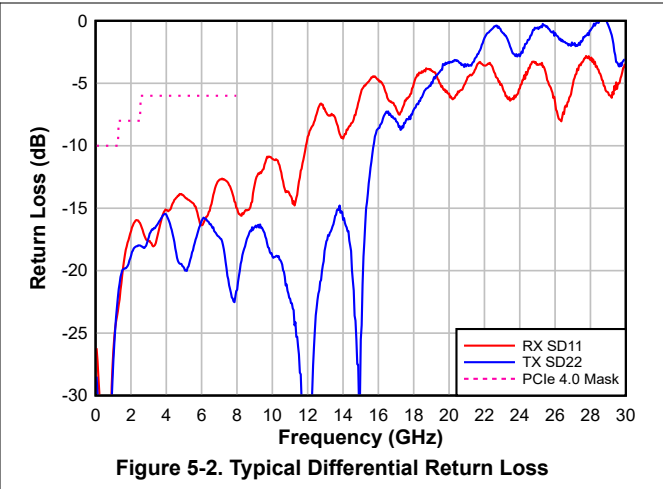
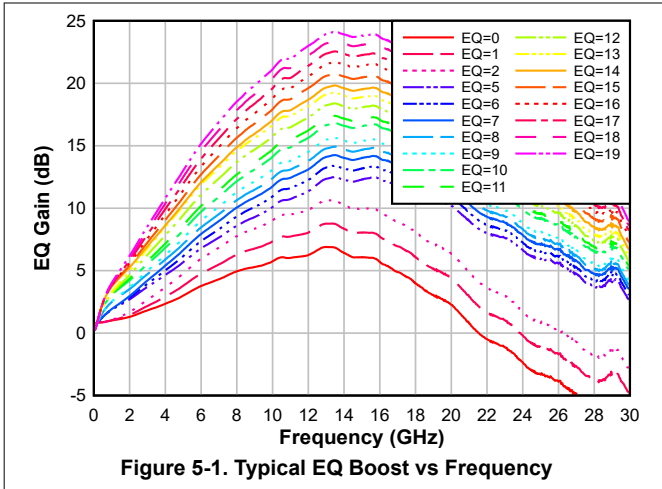
## 5.7 SMBUS/I<sup>2</sup>C Timing Characteristics (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
T <sub>F-M</sub>	Fall time of both SDA and SCL signals	Pullup resistor = 4.7kΩ, C <sub>b</sub> = 10pF		2		ns
t <sub>SU-STO-M</sub>	Stop condition setup time			1.5		μs
<b>EEPROM Timing</b>						
T <sub>EEPROM</sub>	EEPROM configuration load time	Time to assert DONE <sub>n</sub> after READ_EN <sub>n</sub> has been asserted.		7.5		ms
T <sub>POR</sub>	Time to first SMBus access	Power supply stable after initial ramp. Includes initial power-on reset time.		50		ms

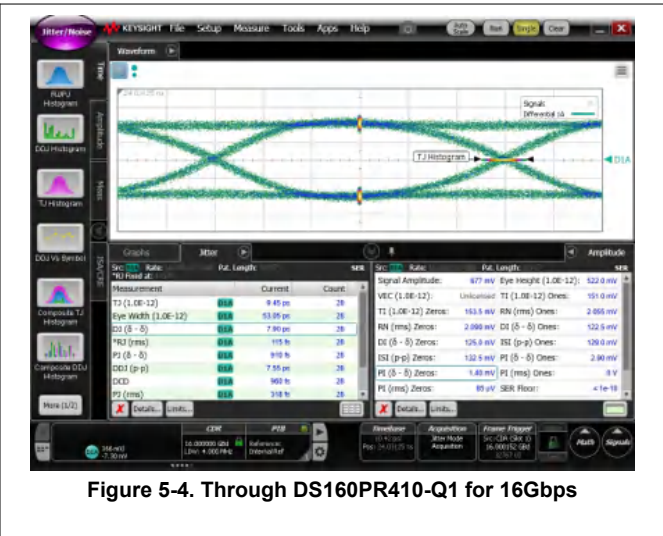
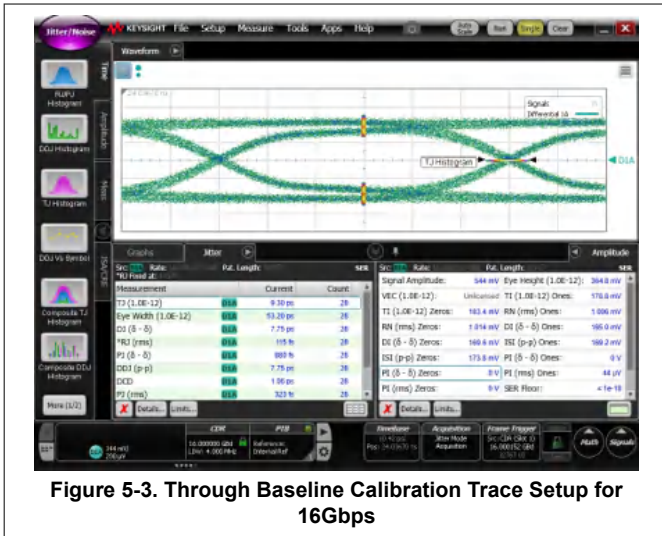
### 5.8 Typical Characteristics

Figure 5-1 shows typical EQ gain curves versus frequency for different EQ settings. Figure 5-2 shows typical differential return loss for Rx and Tx pins.



### 5.9 Typical Jitter Characteristics

Figure 5-3 and Figure 5-4 show eye diagrams at 20Gbps that compare jitter through calibration traces (left), and jitter through DS160PR410-Q1 at TI evaluation boards with minimal channels. The eye diagrams illustrate that DS160PR410-Q1 adds very little random jitter (RJ) - below instrumentation accuracy. Similar total jitter through calibration trace and DUT can be attributed to the residual equalization at EQ = 0 cleaning up DJ for input loss.



## 6 Detailed Description

### 6.1 Overview

The DS160PR410-Q1 is a four channel multi-rate linear repeater with integrated signal conditioning. The device's signal channels operate independently from one another. Each channel includes a continuous-time linear equalizer (CTLE) and a linear output driver, which together compensate for a lossy transmission channel between the source transmitter and the final receiver. The linearity of the data path is specifically designed to preserve any transmit equalization while keeping receiver equalization effective.

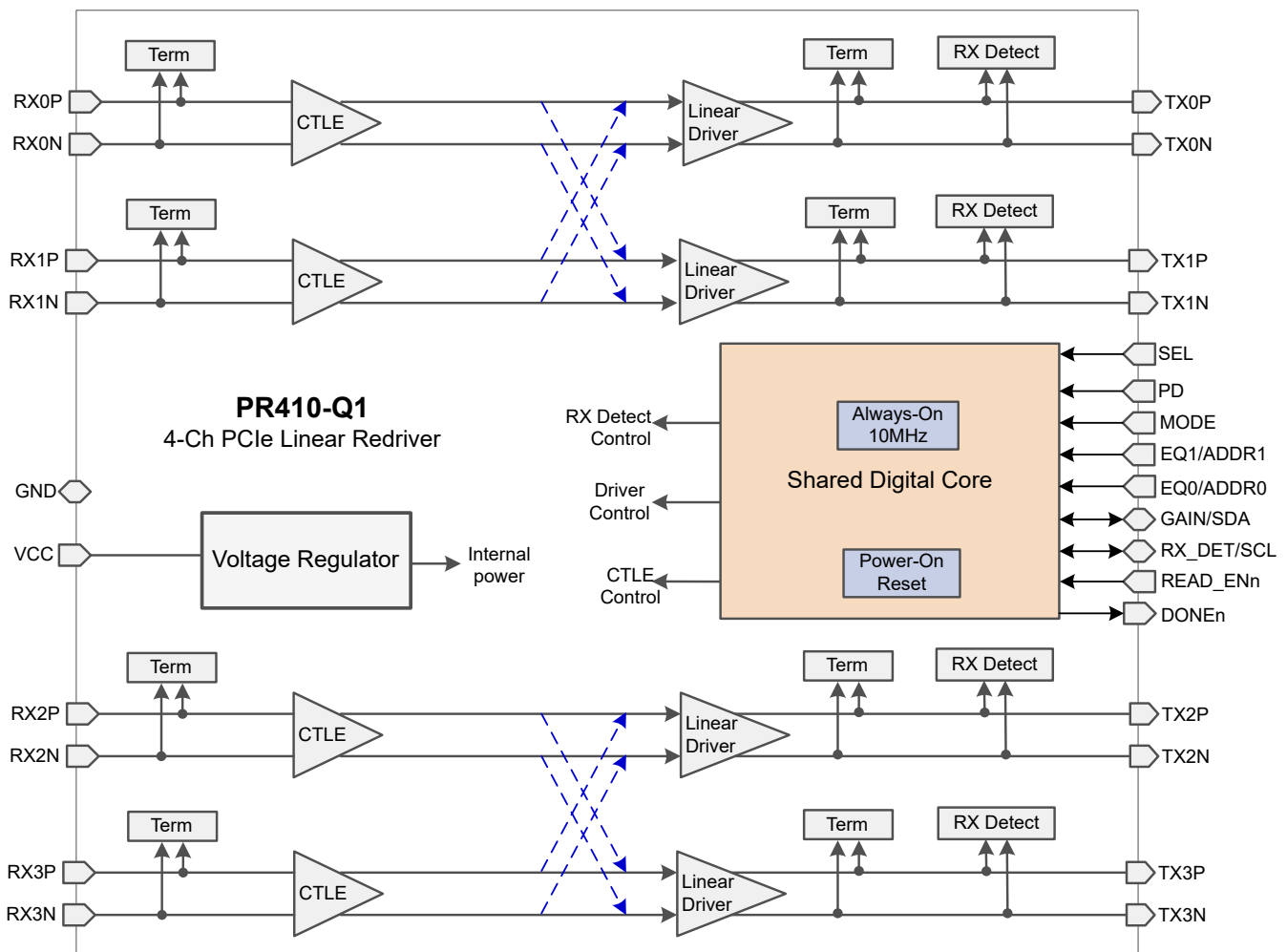
The DS160PR410-Q1 can be configured three different ways:

**Pin mode** – device control configuration is done solely by strap pins. Pin mode is expected to be good enough for many system implementation needs.

**SMBus/I<sup>2</sup>C Controller mode** – device control configuration is read from external EEPROM. When the DS160PR410-Q1 has finished reading from the EEPROM successfully, it will drive the DONE<sub>n</sub> pin LOW. SMBus/I<sup>2</sup>C target operation is available in this mode before, during, or after EEPROM reading. Note: during EEPROM reading, if the external SMBus/I<sup>2</sup>C controller wants to access DS160PR410-Q1 registers, then it must support arbitration. The mode is preferred when software implementation is not desired.

**SMBus/I<sup>2</sup>C Target mode** – provides most flexibility. Requires a SMBus/I<sup>2</sup>C controller device to configure DS160PR410-Q1 though writing to its target address.

### 6.2 Functional Block Diagram



## 6.3 Feature Description

### 6.3.1 Linear Equalization

The DS160PR410-Q1 receivers feature a continuous-time linear equalizer (CTLE) that applies high-frequency boost and low-frequency attenuation to help equalize the frequency-dependent insertion loss effects of the passive channel. The receivers implement two stage linear equalizer for wide range of equalization capability. The equalizer stages also provide flexibility to make subtle modifications of mid-frequency boost for best EQ gain profile match with wide range of channel media characteristics. The EQ profile control feature is only available in SMBus/I<sup>2</sup>C mode. In Pin mode the settings are optimized for FR4 traces.

Table 6-1 provides available equalization boost through EQ control pins or SMBus/I<sup>2</sup>C registers. In Pin Control mode EQ1 and EQ0 pins set equalization boost. In I<sup>2</sup>C mode individual channels can be independently programmed for EQ boost.

**Table 6-1. Equalization Control Settings**

EQ INDEX	EQUALIZATION SETTING						TYPICAL EQ BOOST (dB)  at 8 GHz
	Pin mode		SMBus/I <sup>2</sup> C Mode				
	EQ1	EQ0	eq_stage1_3:0	eq_stage2_2:0	eq_profile_3:0	eq_stage1_bypass	
0	L0	L0	0	0	0	1	3.0
1	L0	L1	1	0	0	1	4.0
2	L0	L2	3	0	0	1	5.5
5	L1	L0	0	0	1	0	6.5
6	L1	L1	1	0	1	0	7.0
7	L1	L2	2	0	1	0	7.5
8	L1	L3	3	0	3	0	8.5
9	L1	L4	4	0	3	0	9.0
10	L2	L0	5	1	7	0	10.0
11	L2	L1	6	1	7	0	10.5
12	L2	L2	8	1	7	0	11.0
13	L2	L3	10	1	7	0	12.0
14	L2	L4	10	2	15	0	12.5
15	L3	L0	11	3	15	0	13.0
16	L3	L1	12	4	15	0	14.0
17	L3	L2	13	5	15	0	14.5
18	L3	L3	14	6	15	0	15.5
19	L3	L4	15	7	15	0	16.0

### 6.3.2 Flat-Gain

The GAIN pin can be used to set the overall data-path flat gain (DC and AC) of the DS160PR410-Q1 when the device is in Pin mode. In I<sup>2</sup>C mode each channel can be independently set. Table 6-2 provides flat gain control configuration settings. In the default recommendation for most systems will be GAIN = L4 (float) that provides flat gain of 0.6dB.

The flat-gain and equalization of the DS160PR410-Q1 must be set such that the output signal swing at DC and high frequency does not exceed the DC and AC linearity ranges of the devices, respectively.

**Table 6-2. Flat Gain Configuration Settings**

Pin mode GAIN	I <sup>2</sup> C Mode flat_gain_2:0	Flat Gain
L0	0	-5.6dB
L1	1	-3.8dB
L2	3	-1.3dB
L3	7	+2.5dB
L4 (float)	5	0.6dB (default recommendation)

### 6.3.3 Receiver Detect State Machine

The DS160PR410-Q1 deploys an Rx detect state machine that governs the Rx detection cycle as defined in the PCI express specifications. At power up or after a manual PD or SEL toggle the redriver determines whether or not a valid PCI express termination is present at the far end receiver. The RX\_DET pin of DS160PR410-Q1 provides additional flexibility for system designers to appropriately set the device in desired mode as provided in Table 6-3. For most applications the RX\_DET pin can be left floating for default settings. In SMBus/I<sup>2</sup>C mode each channel can be configured independently.

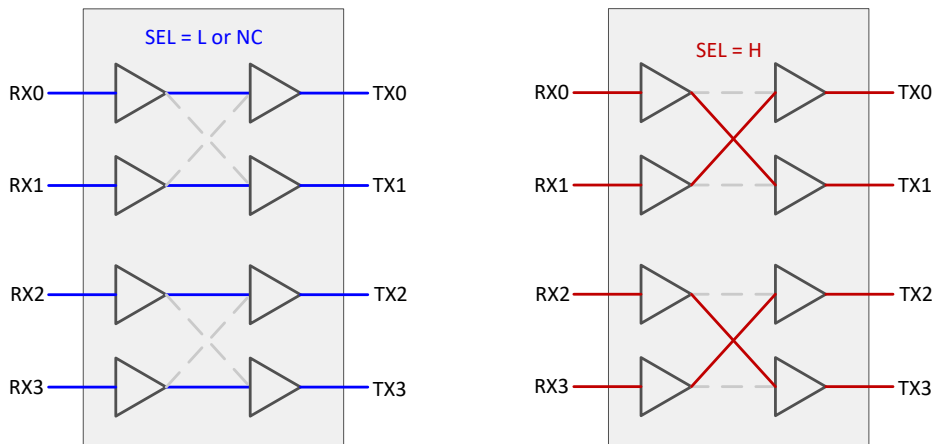
**Table 6-3. Receiver Detect State Machine Settings**

PD	RX_DET	Rx Common-mode Impedance	COMMENTS
L	L0	Always 50Ω	PCI Express Rx detection state machine is disabled. Recommended for non PCIe interface use case where the DS160PR410-Q1 is used as buffer with equalization.
L	L1	Pre Detect: Hi-Z Post Detect: 50Ω.	Outputs polls until 3 consecutive valid detections
L	L2	Pre Detect: Hi-Z Post Detect: 50Ω.	Outputs polls until 2 consecutive valid detections
L	L3	NA	Reserved
L	L4 (Float)	Pre Detect: Hi-Z Post Detect: 50Ω.	Tx polls every $\approx 150\mu s$ until valid termination is detected. Rx CM impedance held at Hi-Z until detection Reset by asserting PD high for $200\mu s$ then low.
H	X	Hi-Z	Set their Rx impedance to Hi-Z

In PCIe applications PD pins can be connected to PCIe sideband signals PERST# with inverted polarity or one or more appropriate PRSNTx# signals to achieve desired RX detect functionality.

### 6.3.4 Cross Point

The DS160PR410-Q1 provides dual 2x2 cross-point function. Using SEL pin the 4 channel signal paths can be configured as straight connection or cross connections as shown in Figure 6-1.



**Figure 6-1. DS160PR410-Q1 Signal Flow Diagram for Cross-Point Mux Operation**

## 6.4 Device Functional Modes

### 6.4.1 Active PCIe Mode

The device is in normal operation with PCIe state machine enabled by RX\_DET = L1/L2/L4. In this mode PD pin are driven low in a system (for example, by PCIE connector *PRSNTx#* or fundamental reset *PERST#* signal). In this mode, the DS160PR410-Q1 redrives and equalizes PCIe Rx or Tx signals to provide better signal integrity.

### 6.4.2 Linear Equalizer (Buffer) Mode

The device is in normal operation with PCIe state machine disabled by RX\_DET = L0. This mode is recommended for non-PCIe use cases. In this mode the device is working as a buffer to provide linear equalization to improve signal integrity.

### 6.4.3 Standby Mode

The device is in standby mode invoked by PD = H. In this mode, the device is in standby mode conserving power.

## 6.5 Programming

### 6.5.1 Pin Mode

The DS160PR410-Q1 can be fully configured through pin-strap pins. In this mode the device uses 2-level and 5-level pins for device control and signal integrity optimum settings.

#### 6.5.1.1 Five-Level Control Inputs

The DS160PR410-Q1 has five (EQ0, EQ1, GAIN, MODE, and RX\_DET) 5-level input pins that are used to control the configuration of the device. These 5-level inputs use a resistor divider to help set the 5 valid levels and provide a wider range of control settings. External resistors must be of 10% tolerance or better. The EQ0, EQ1, GAIN, and RX\_DET pins are sampled at power-up only. The MODE pin can be exercised at device power up or in normal operation mode.

**Table 6-4. 5-Level Control Pin Settings**

LEVEL	SETTING
L0	1kΩ to GND
L1	8.25kΩ to GND
L2	24.9kΩ to GND
L3	75kΩ to GND
L4	F (Float)

### 6.5.2 SMBUS/I<sup>2</sup>C Register Control Interface

If MODE = L2 (SMBus/I<sup>2</sup>C Target control mode), then the DS160PR410-Q1 is configured through a standard I<sup>2</sup>C or SMBus interface that may operate up to 400kHz. The target address of the DS160PR410-Q1 is determined by the pin strap settings on the ADDR1 and ADDR0 pins. The sixteen possible target addresses for each channel bank of the DS160PR410-Q1 are provided in [Table 6-5](#). In SMBus/I<sup>2</sup>C modes the SCL and SDA pins must be pulled up to a 3.3V supply with a pull-up resistor. The value of the resistor depends on total bus capacitance. 4.7kΩ is a good first approximation for a bus capacitance of 10pF.

**Table 6-5. SMBUS/I<sup>2</sup>C Target Address Settings**

ADDR1	ADDR0	7-bit Target Address
L0	L0	0x18
L0	L1	0x1A
L0	L2	0x1C
L0	L3	0x1E
L1	L0	0x20
L1	L1	0x22
L1	L2	0x24
L1	L3	0x26
L2	L0	0x28
L2	L1	0x2A
L2	L2	0x2C
L2	L3	0x2E
L3	L0	0x30
L3	L1	0x32
L3	L2	0x34
L3	L3	0x36
X	L4	Reserved

The DS160PR410-Q1 has two types of registers:

- **Shared Registers:** these registers can be accessed at any time and are used for device-level configuration, status read back, control, or to read back the device ID information.
- **Channel Registers:** these registers are used to control and configure specific features for each individual channel. All channels have the same register set and can be configured independent of each other or configured as a group through broadcast writes to Bank 0 or Bank 1.

The DS160PR410-Q1 features four channels.

Channel Registers Base Address	Channel Access
0x00	Channel 0 registers
0x20	Channel 1 registers
0x40	Channel 2 registers
0x60	Channel 3 registers
0x80	Broadcast write channel Bank 0 registers, read channel 0 registers
0xA0	Broadcast write channel 0-1 registers, read channel 0 registers
0xC0	Broadcast write channel 2-3 registers, read channel 2 registers
0xE0	Channels 0-3 Share registers

### 6.5.2.1 Shared Registers

**Table 6-6. General Registers (Offset = 0xE2)**

Bit	Field	Type	Reset	Description
7	RESERVED	R	0x0	Reserved
6	rst_i2c_regs	R/W/SC	0x0	Device reset control: Reset all I <sup>2</sup> C registers to default values (self-clearing).
5	rst_i2c_mas	R/W/SC	0x0	Reset I <sup>2</sup> C controller (self-clearing).
4-1	RESERVED	R	0x0	Reserved
0	frc_eeprm_rd	R/W/SC	0x0	Override MODE and READ_ENn status to force manual EEPROM configuration load.

**Table 6-7. EEPROM\_Status Register (Offset = 0xE3)**

Bit	Field	Type	Reset	Description
7	eecfg_cmplt	R	0x0	EEPROM load complete.
6	eecfg_fail	R	0x0	EEPROM load failed.
5	eecfg_atmpt_1	R	0x0	Number of attempts made to load EEPROM image.
4	eecfg_atmpt_0	R	0x0	see MSB
3	eecfg_cmplt	R	0x0	EEPROM load complete 2.
2	eecfg_fail	R	0x0	EEPROM load failed 2.
1	eecfg_atmpt_1	R	0x0	Number of attempts made to load EEPROM image 2.
0	eecfg_atmpt_0	R	0x0	see MSB

**Table 6-8. DEVICE\_ID0 Register (Offset = 0xF0)**

Bit	Field	Type	Reset	Description
7-4	RESERVED	R	0x0	Reserved
3	device_id0_3	R	0x0	Device ID0 [3:1]: 011
2	device_id0_2	R	0x1	see MSB
1	device_id0_1	R	0x1	see MSB
0	RESERVED	R	X	Reserved

**Table 6-9. DEVICE\_ID1 Register (Offset = 0xF1)**

Bit	Field	Type	Reset	Description
7	device_id[7]	R	0x0	Device ID 0010 1001: DS160PR410-Q1
6	device_id[6]	R	0x0	see MSB
5	device_id[5]	R	0x1	see MSB
4	device_id[4]	R	0x0	see MSB
3	device_id[3]	R	0x1	see MSB
2	device_id[2]	R	0x0	see MSB
1	device_id[1]	R	0x0	see MSB
0	device_id[0]	R	0x0	see MSB

### 6.5.2.2 Channel Registers

**Table 6-10. RX Detect Status Register (Channel Register Base + Offset = 0x00)**

Bit	Field	Type	Reset	Description
7	rx_det_comp_p	R	0x0	Rx Detect positive data pin status: 0: Not detected 1: Detected – the value is latched
6	rx_det_comp_n	R	0x0	Rx Detect negative data pin status: 0: Not detected 1: Detected – the value is latched
5-0	RESERVED	R	0x0	Reserved

**Table 6-11. EQ Gain Control Register (Channel Register Base + Offset = 0x01)**

Bit	Field	Type	Reset	Description
7	eq_stage1_bypass	R/W	0x0	Enable EQ stage 1 bypass: 0: Bypass disabled 1: Bypass enabled
6	eq_stage1_3	R/W	0x0	EQBoost stage 1 control See <a href="#">Table 6-1</a> for details
5	eq_stage1_2	R/W	0x0	
4	eq_stage1_1	R/W	0x0	
3	eq_stage1_0	R/W	0x0	
2	eq_stage2_2	R/W	0x0	EQ Boost stage 2 control See <a href="#">Table 6-1</a> for details
1	eq_stage2_1	R/W	0x0	
0	eq_stage2_0	R/W	0x0	

**Table 6-12. EQ Gain / Flat Gain Control Register (Channel Register Base + Offset = 0x03)**

Bit	Field	Type	Reset	Description
7	RESERVED	R	0x0	Reserved
6	eq_profile_3	R/W	0x0	EQ mid-frequency boost profile See <a href="#">Table 6-1</a> for details
5	eq_profile_2	R/W	0x0	
4	eq_profile_1	R/W	0x0	
3	eq_profile_0	R/W	0x0	
2	flat_gain_2	R/W	0x1	Flat gain select: See <a href="#">Table 6-2</a> for details
1	flat_gain_1	R/W	0x0	
0	flat_gain_0	R/W	0x1	

**Table 6-13. RX Detect Control Register (Channel Register Base + Offset = 0x04)**

Bit	Field	Type	Reset	Description
7-3	RESERVED	R	0x0	Reserved

**Table 6-13. RX Detect Control Register (Channel Register Base + Offset = 0x04) (continued)**

Bit	Field	Type	Reset	Description
2	mr_rx_det_man	R/W	0x0	Manual override of rx_detect_p/n decision: 0: rx detect state machine is enabled 1: rx detect state machine is overridden – always valid RX termination detected
1	en_rx_det_count	R/W	0x0	Enable additional RX detect polling 0: Additional RX detect polling disabled 1: Additional RX detect polling enabled
0	sel_rx_det_count	R/W	0x0	Select number of valid RX detect polls – gated by en_rx_det_count = 1 0: Device transmitters poll until 2 consecutive valid detections 1: Device transmitters poll until 3 consecutive valid detections

**Table 6-14. PD Override Register (Channel Register Base + Offset = 0x05)**

Bit	Field	Type	Reset	Description
7	device_en_override	R/W	0x0	Enable power down overrides through SMBus/I <sup>2</sup> C 0: Manual override disabled 1: Manual override enabled
6-0	device_en	R/W	0x111111	Manual power down of redriver various blocks – gated by device_en_override = 1 111111: All blocks are enabled 000000: All blocks are disabled

**Table 6-15. Bias Register (Channel Register Base + Offset = 0x06)**

Bit	Field	Type	Reset	Description
5-3	Bias current	R/W	0x100	Control bias current Set 001 for best performance
7,6,2-0	Reserved	R/W	0x00000	Reserved

### 6.5.3 SMBus/I<sup>2</sup>C Controller Mode Configuration (EEPROM Self Load)

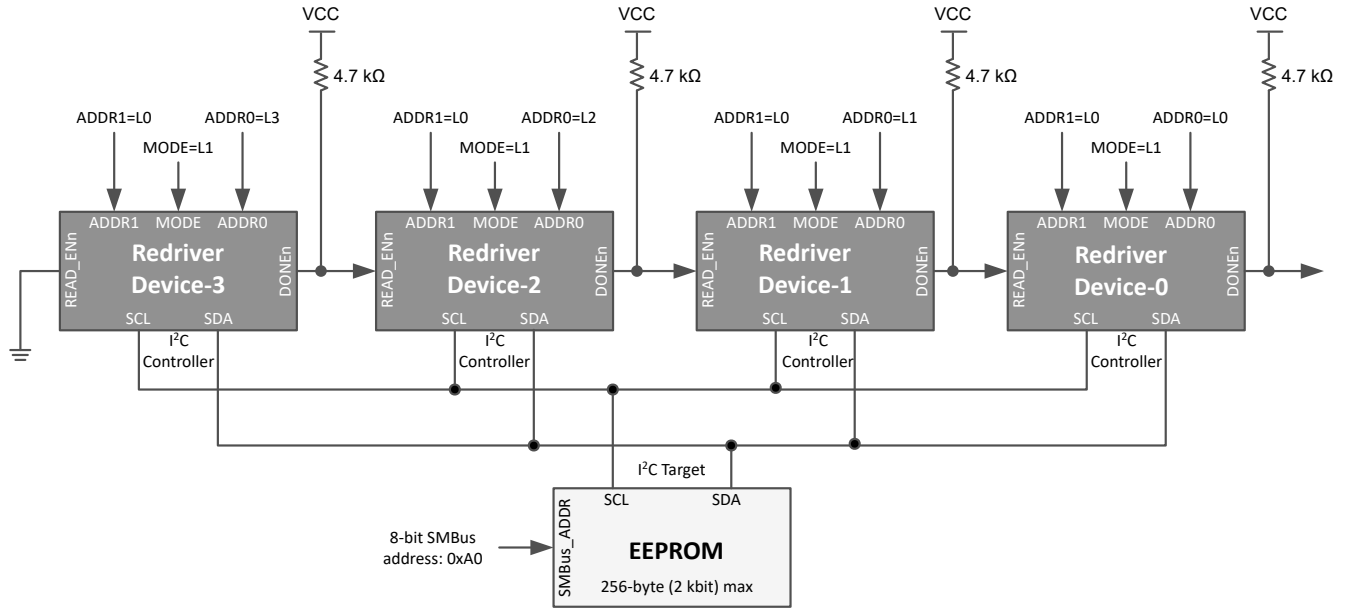
The DS160PR410-Q1 can also be configured by reading from EEPROM. To enter into this mode MODE pin must be set to L1. The EEPROM load operation only happens once after the device's initial power-up. If the DS160PR410-Q1 is configured for SMBus Controller mode, then it will remain in the SMBus IDLE state until the READ\_ENn pin is asserted to LOW. After the READ\_ENn pin is driven LOW, the DS160PR410-Q1 becomes an SMBus controller and attempts to self-configure by reading the device settings stored in an external EEPROM (SMBus 8-bit address 0xA0). When the DS160PR410-Q1 has finished reading from the EEPROM successfully, it will drive the DONEn pin LOW. SMBus/I<sup>2</sup>C target operation is available in this mode before, during, or after EEPROM reading. Note: during EEPROM reading, if the external SMBus/I<sup>2</sup>C controller wants to access DS160PR410-Q1 registers, then it must support arbitration.

When designing a system for using the external EEPROM, the user must follow these specific guidelines:

- EEPROM size of 2kb (256 × 8-bit) is recommended.
- Set MODE = L1, configure for SMBus Controller mode.
- The external EEPROM device address byte must be 0xA0 and capable of 400kHz operation at 3.3V supply
- In SMBus/I<sup>2</sup>C modes the SCL and SDA pins must be pulled up to a 3.3V supply with a pull-up resistor. The value of the resistor depends on total bus capacitance. 4.7kΩ is a good first approximation for a bus capacitance of 10pF.

Figure 6-2 shows a use case with four DS160PR410-Q1 to implement a PCIe x8 or two x4 configurations, but the user can cascade any number of DS160PR410-Q1 devices in a similar way. Tie the READ\_ENn pin of the first device low to automatically initiate EEPROM read at power up. Alternatively, the READ\_ENn pin of the first device can also be controlled by a micro-controller to initiate the EEPROM read manually. Leave the DONEn pin

of the final device floating, or connect the pin to a micro-controller input to monitor the completion of the final EEPROM read.



**Figure 6-2. Daisy Chain Four DS160PR410-Q1 Devices to Read from Single EEPROM in Two x4 or One x8 Link Configuration**

## 7 Application and Implementation

### Note

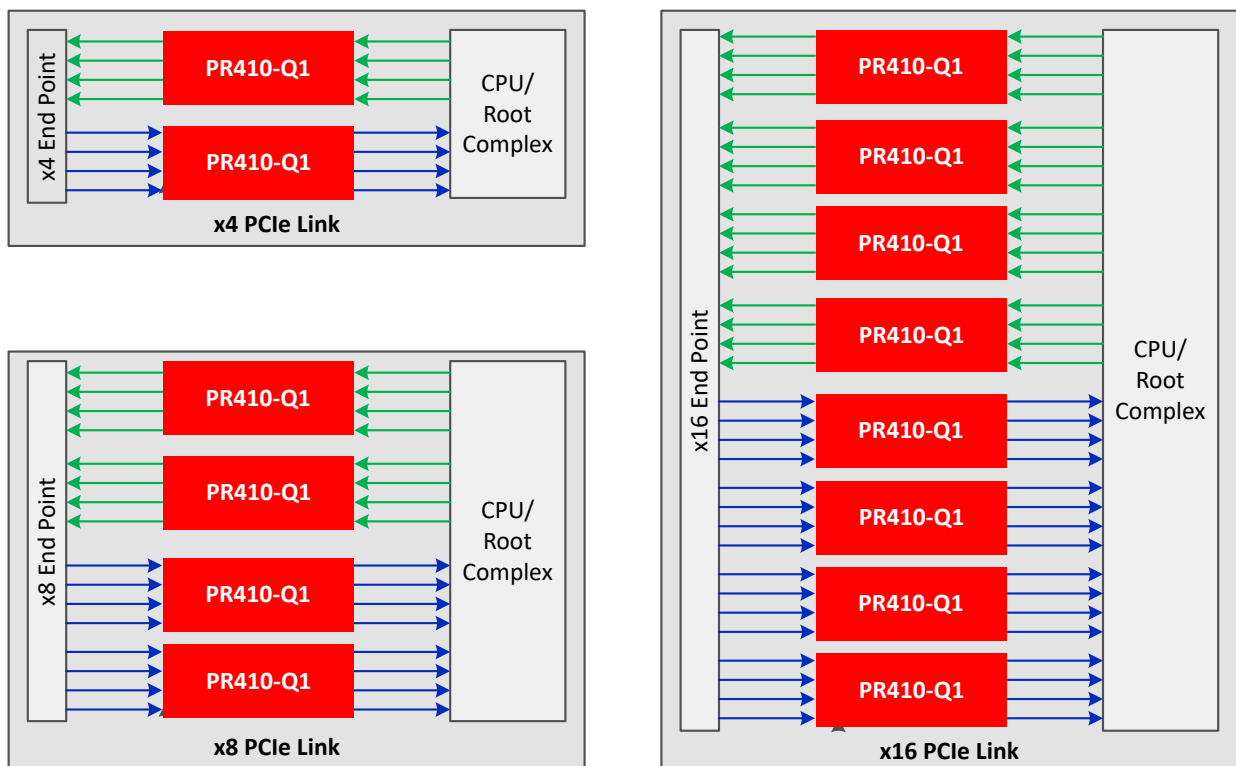
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 7.1 Application Information

The DS160PR410-Q1 is a high-speed linear repeater which extends the reach of differential channels impaired by loss from transmission media like PCBs and cables. It can be deployed in a variety of different systems. The following sections outline typical applications and their associated design considerations.

### 7.2 Typical Applications

The DS160PR410-Q1 is a PCI Express linear redriver that can also be configured as interface agnostic redriver by disabling its Rx detect feature. The DS160PR410-Q1 is a protocol agnostic 4 channel linear redriver with PCI Express receiver-detect capability. Its protocol agnostic nature allows it to be used in PCI Express x4, x8, and x16 applications. [Figure 7-1](#) shows how a number of DS160PR410-Q1 devices can be used to obtain signal conditioning for PCI Express buses of varying widths.



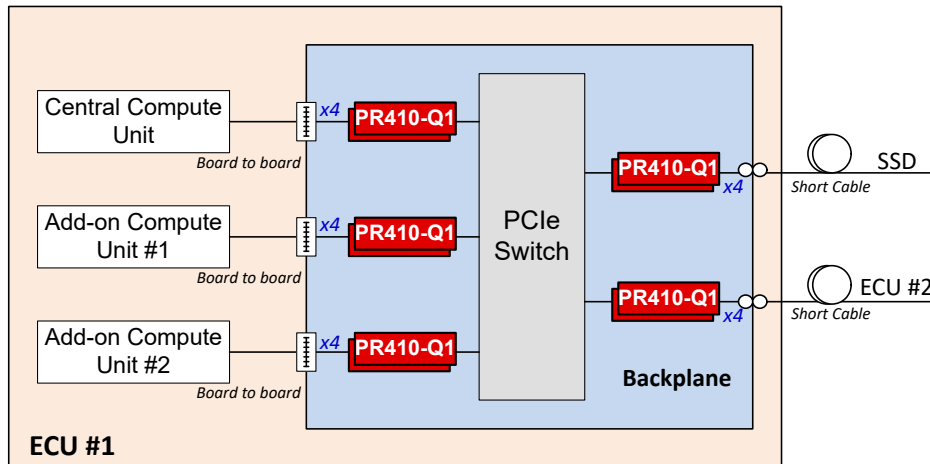
**Figure 7-1. PCI Express x4, x8 and x16 Use Cases Using DS160PR410-Q1**

### Note

all four channels of the DS160PR410-Q1 flow in same direction. Therefore, if the device is used for x4 configuration with two devices, then PD of both devices need to be connected together to implement PCIe state machine.

## 7.2.1 x4 Lane Configuration

The DS160PR410-Q1 can be used in automotive applications to boost transmit and receive signals to increase the reach of the host or root complex processor to PCIe Express end points (EPs). Figure 7-2 shows an automotive electronic control unit (ECU) where PCIe link are used to interconnect multiple compute units within the ECU using board to board connectors where the DS160PR410-Q1 is providing signal conditioning function. The redriver can also enable PCIe links outside of the ECU using short cables. In this example, x4 links are shown for illustration, but other bus widths are also possible.



**Figure 7-2. PCIe x4 Links in an Automotive Electronic Control Unit**

The following sections outline detailed procedures and design requirements for a typical PCIe x4 lane configuration. However, the design recommendations can be used in any lane configuration.

### 7.2.1.1 Design Requirements

As with any high-speed design, there are many factors which influence the overall performance. The following list indicates critical areas for consideration during design.

- Use 85Ω impedance traces when interfacing with PCIe CEM connectors. Length matching on the P and N traces must be done on the single-end segments of the differential pair.
- Use a uniform trace width and trace spacing for differential pairs.
- Place AC-coupling capacitors near the receiver end of each channel segment to minimize reflections.
- For PCIe AC-coupling capacitors of 220nF are recommended. Set the maximum body size to 0402 and add a cutout void on the GND plane below the landing pad of the capacitor to reduce parasitic capacitance to GND.
- Back-drill connector vias and signal vias to minimize stub length.
- Use reference plane vias to make a low inductance path for the return current.

### 7.2.1.2 Detailed Design Procedure

In PCIe Gen 3.0, and 4.0 applications, the specification requires Rx-Tx (of root-complex and endpoint) link training to establish and optimize signal conditioning settings at 8Gbps and 16Gbps respectively. In link training, the Rx partner requests a series of FIR – preshoot and de-emphasis coefficients (10 Presets) from the Tx partner. The Rx partner includes CTLE and DFE. The link training pre-conditions the signal, with an equalized link between the root-complex and endpoint resulting an optimized link. Note that there is no link training in PCIe Gen 1.0 (2.5Gbps) or PCIe Gen 2.0 (5.0Gbps) applications.

For operation in Gen 3.0, and 4.0 links, the DS160PR410-Q1 is designed with linear data-path to pass the Tx Preset signaling (by root complex and end point) onto the Rx (of root complex and end point) for the PCIe Gen 3.0, and 4.0 link to train and optimize the equalization settings. The linear redriver DS160PR410-Q1 helps extend the PCB trace reach distance by boosting the attenuated signals with its equalization, which allows the user to recover the signal by the link partner's Rx more easily. The device must be placed in between the Tx and Rx (of root complex and end point) in such a way that both Rx and Tx signal swings stay within the linearity range of the device. Adjustments to the DS160PR410-Q1 EQ setting should be performed based on the channel

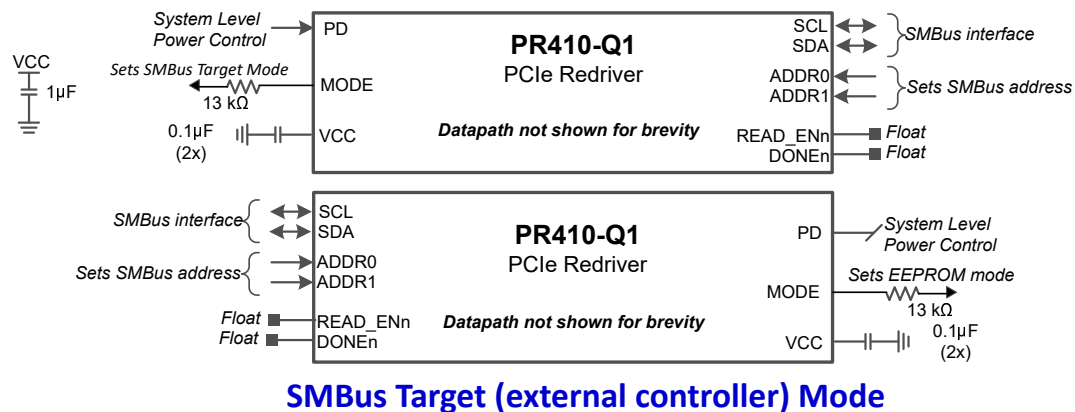
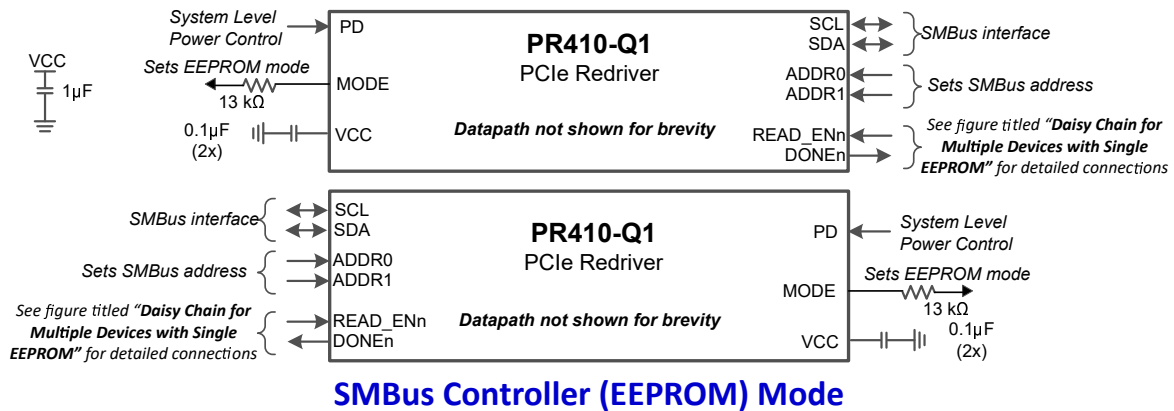
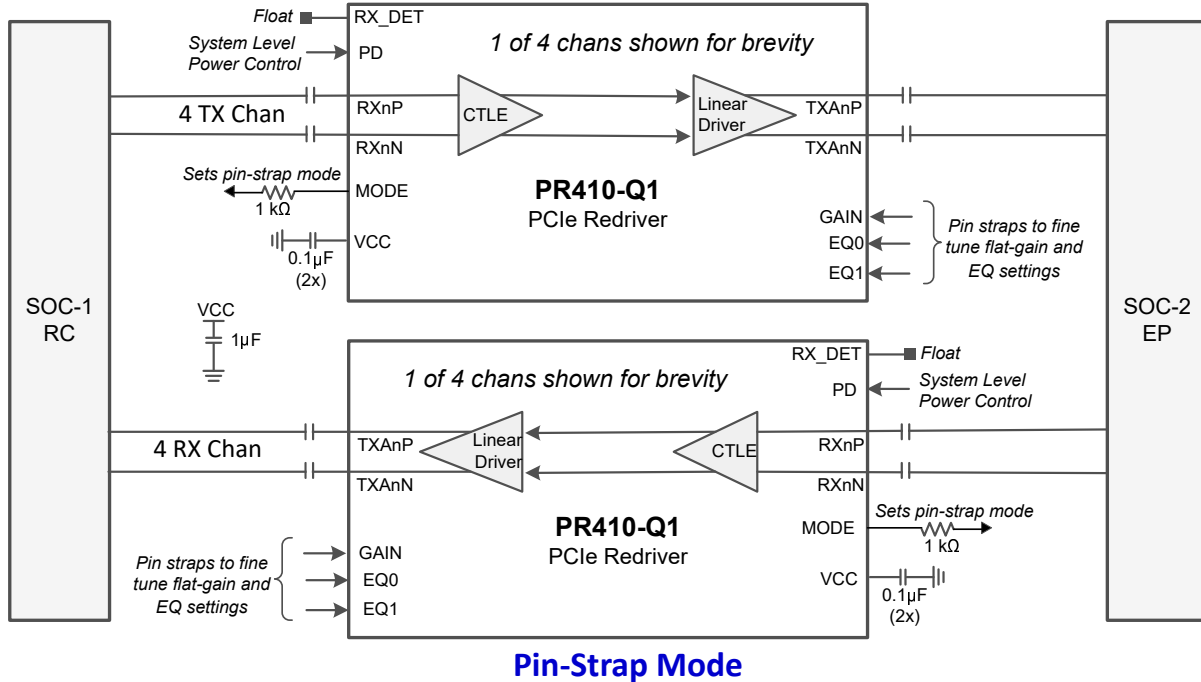
loss to optimize the eye opening in the Rx partner. The available EQ gain settings are provided in [Table 6-1](#). For most PCIe systems the default flat gain setting 0.6dB (GAIN = floating) would be sufficient. However, a flat gain attenuation can be used to apply extra equalization when needed to keep the data-path linear.

The DS160PR410-Q1 can be optimized for a given system using the three configuration modes – Pin mode, SMBus/I<sup>2</sup>C Controller mode, and SMBus/I<sup>2</sup>C Target mode. In SMBus/I<sup>2</sup>C modes the SCL and SDA pins must be pulled up to a 3.3V supply with a pull-up resistor. The value of the resistor depends on total bus capacitance. 4.7kΩ is a good first approximation for a bus capacitance of 10pF.

In PCIe applications PD pin can be connected to PCIe sideband signals PERST# with inverted polarity or one or more appropriate PRSNTx# signals to achieve desired RX detect functionality.

The DS160PR410-Q1 can be optimized for a given system using the three configuration modes – Pin mode, SMBus/I<sup>2</sup>C Controller mode, and SMBus/I<sup>2</sup>C Target mode. In SMBus/I<sup>2</sup>C modes the SCL and SDA pins must be pulled up to a 3.3V supply with a pull-up resistor. The value of the resistor depends on total bus capacitance. 4.7kΩ is a good first approximation for a bus capacitance of 10pF.

[Figure 7-3](#) shows a simplified schematic for x4 lane configuration in pin-strap, EEPROM and SMBus Target modes.



**Figure 7-3. Simplified Schematic for PCIe x4 Lane Configuration in Pin-strap, EEPROM and SMBus Target Modes**

### 7.2.1.3 Application Curves

The DS160PR410-Q1 is a linear redriver that can be used to extend channel reach of a PCIe link. Normally, PCIe-compliant Tx and Rx are equipped with signal-conditioning functions and can handle channel losses of up to 28dB at 8GHz. With the DS160PR410-Q1, the total channel loss between a PCIe root complex and an end point can be extended by up to 12dB at 8GHz.

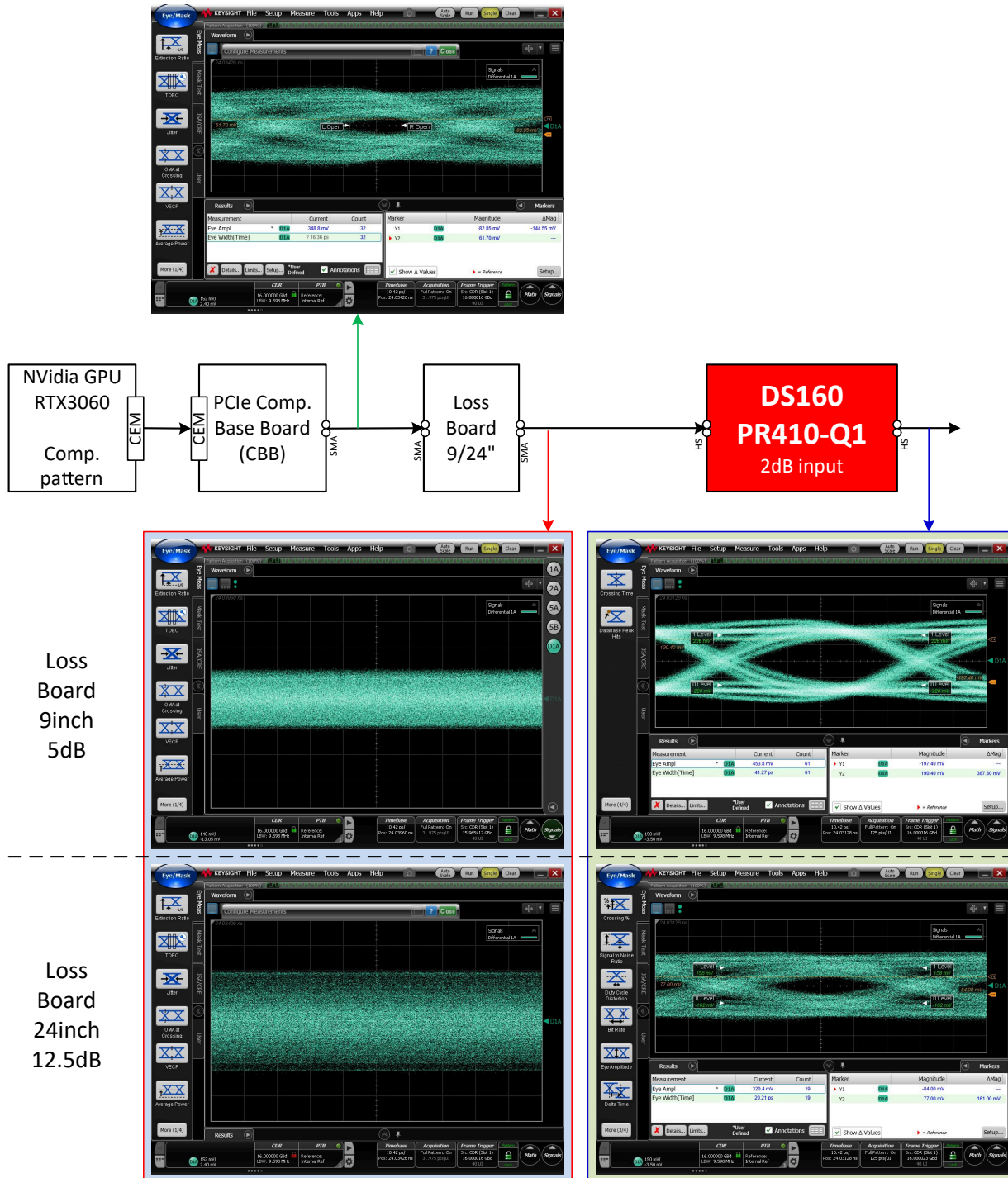


Figure 7-4. Illustration of equalization by the DS160PR410-Q1

To demonstrate the reach extension capability of the DS160PR410-Q1, a setup is constructed where a GPU card is used as a PCIe root complex sending PCIe 4.0 compliance patterns as illustrated in [Figure 7-4](#). The output of the GPU card is captured through a PCIe compliance baseboard (CBB). Additional loss is inserted by a SMA loss board. The DS160PR410-Q1 is removing jitter to open the eye diagrams closed by added jitter from board loss. [Table 7-1](#) shows eye opening information.

**Table 7-1. PCIe 4.0 Reach Extension using the DS160PR410-Q1**

Setup	GPU output eye through CBB	Eye after loss board (redriver input)	Redriver output eye
9 inch loss board (5dB) Redriver EQ = 17	Eye width 16.4ps Eye height 145mV	closed	Eye width 41.3ps Eye height 388mV
24 inch loss board (12.5dB) Redriver EQ = 19			Eye width 20.2ps Eye height 161mV

### 7.3 Power Supply Recommendations

Follow these general guidelines when designing the power supply:

1. The power supply must be designed to provide the operating conditions outlined in the recommended operating conditions section in terms of DC voltage, AC noise, and start-up ramp time.
2. The DS160PR410-Q1 does not require any special power supply filtering, such as ferrite beads, provided that the recommended operating conditions are met. Only standard supply decoupling is required. Typical supply decoupling consists of a 0.1 $\mu$ F capacitor per VCC pin, one 1.0 $\mu$ F bulk capacitor per device, and one 10 $\mu$ F bulk capacitor per power bus that delivers power to one or more DS160PR410-Q1 devices. The local decoupling (0.1 $\mu$ F) capacitors must be connected as close to the VCC pins as possible and with minimal path to the DS160PR410-Q1 ground pad.
3. The DS160PR410-Q1 voltage regulator output pins require decoupling caps of 0.1 $\mu$ F near each pin. The regulator is only for internal use. Do not use to provide power to any external component.

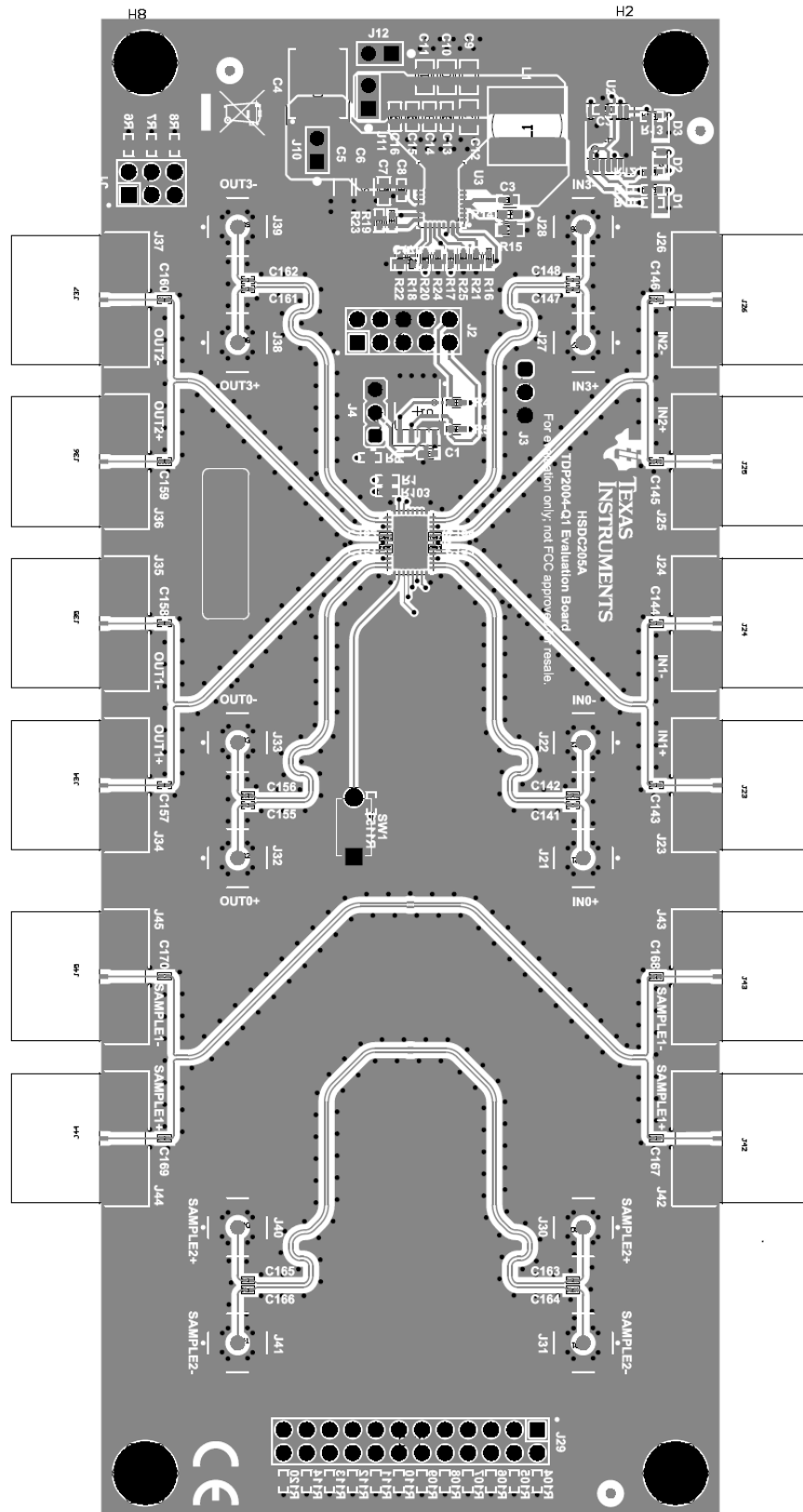
### 7.4 Layout

#### 7.4.1 Layout Guidelines

The following guidelines should be followed when designing the layout:

1. Decoupling capacitors should be placed as close to the VCC pins as possible. Placing the decoupling capacitors directly underneath the device is recommended if the board design permits.
2. High-speed differential signals TXnP/TXnN and RXnP/RXnN should be tightly coupled, skew matched, and impedance controlled.
3. Vias should be avoided when possible on the high-speed differential signals. When vias must be used, take care to minimize the via stub, either by transitioning through most or all layers or by back drilling.
4. GND relief can be used (but is not required) beneath the high-speed differential signal pads to improve signal integrity by counteracting the pad capacitance.
5. GND vias should be placed directly beneath the device connecting the GND plane attached to the device to the GND planes on other layers. This has the added benefit of improving thermal conductivity from the device to the board.

### 7.4.2 Layout Example



**Figure 7-5. DS160PR410-Q1 Layout Example – TI Evaluation Board**

## 8 Device and Documentation Support

### 8.1 Documentation Support

#### 8.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, [DS160PR810 Programming Guide](#)
- Texas Instruments, [Understanding EEPROM Programming for DS160PR810 PCI-Express Gen-4 Redriver](#)

### 8.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](#). Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 8.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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### 8.4 Trademarks

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### 8.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 8.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

## 9 Revision History

DATE	REVISION	NOTES
June 2025	*	Initial Release

## 10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

## GENERIC PACKAGE VIEW

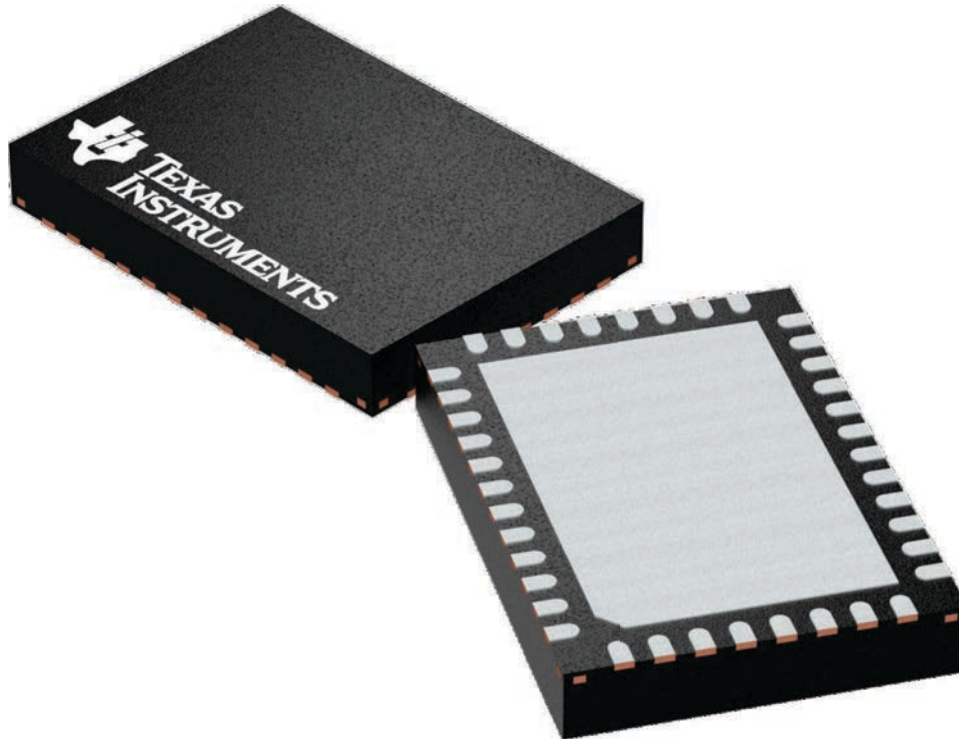
**RGF 40**

**VQFN - 1 mm max height**

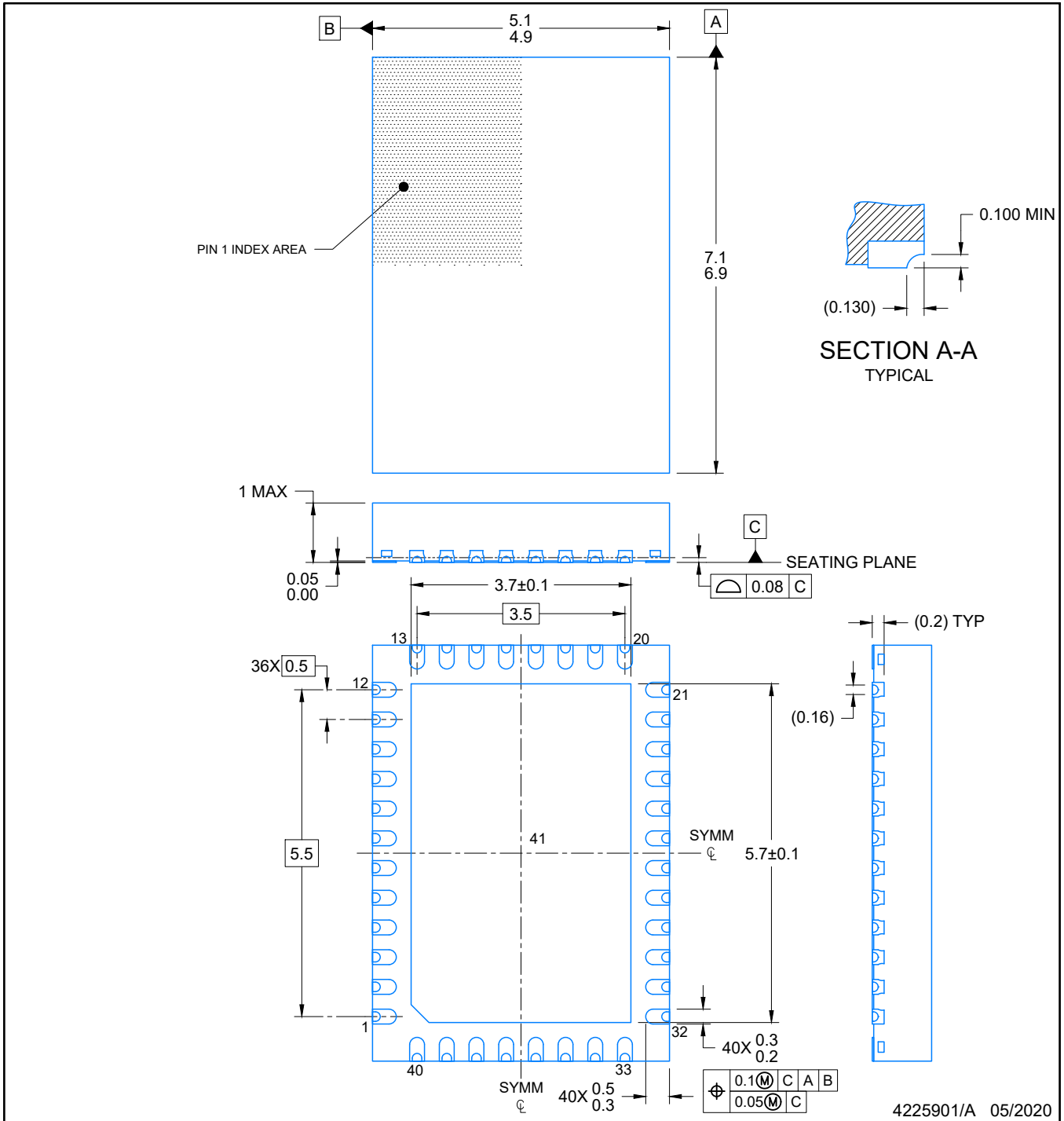
5 x 7, 0.5 mm pitch

PLASTIC QUAD FLAT PACK- NO LEAD

This image is a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.



PLASTIC QUAD FLATPACK- NO LEAD



NOTES:

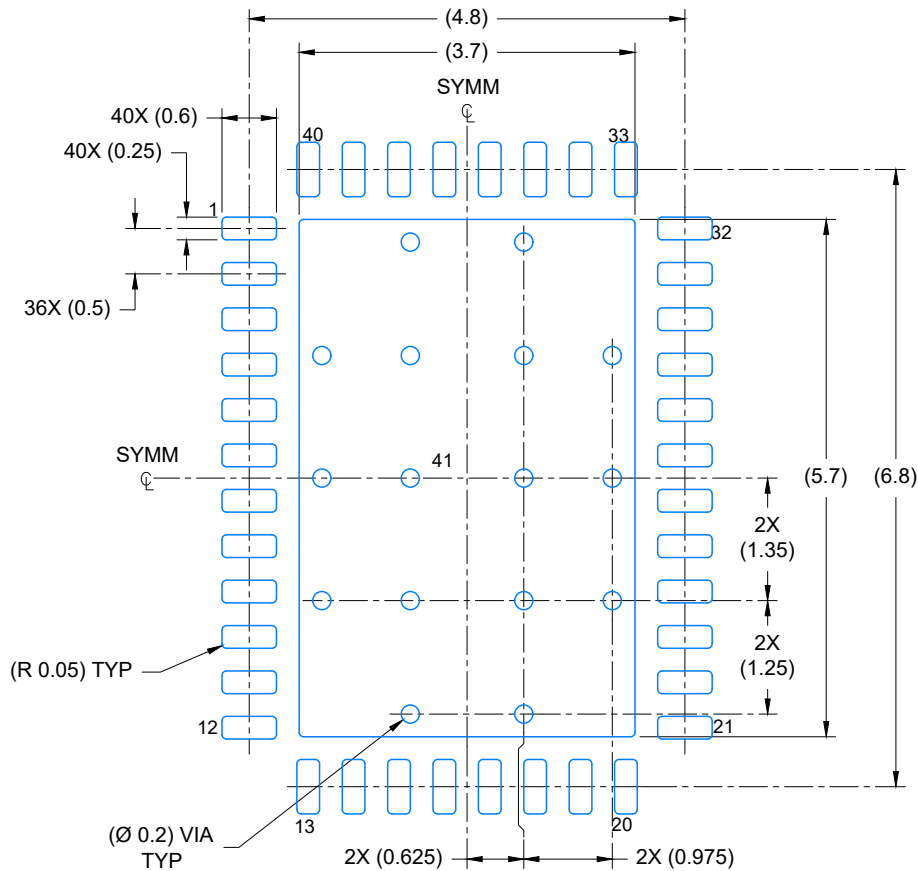
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

# EXAMPLE BOARD LAYOUT

VQFN - 1 mm max height

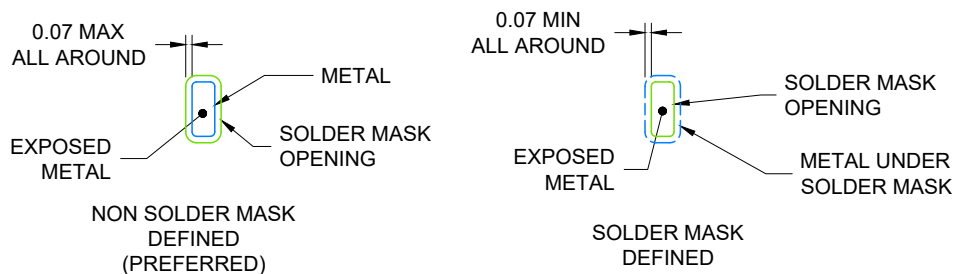
RGF0040F

PLASTIC QUAD FLATPACK- NO LEAD



## LAND PATTERN EXAMPLE

EXPOSED METAL SHOWN  
SCALE: 12X



## SOLDER MASK DETAILS

4225901/A 05/2020

NOTES: (continued)

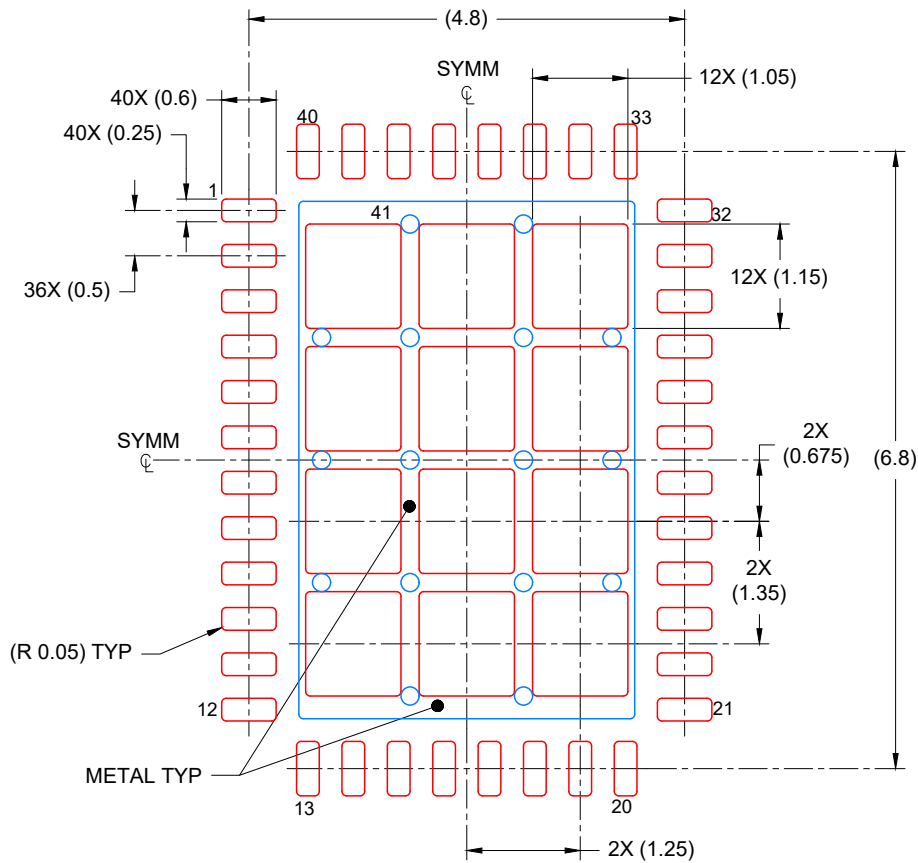
- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

# EXAMPLE STENCIL DESIGN

RGF0040F

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK- NO LEAD



SOLDER PASTE EXAMPLE  
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD  
69% PRINTED COVERAGE BY AREA  
SCALE: 12X

4225901/A 05/2020

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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